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Observation of Dislocation Related Dissipation Mechanism in High Temperature Mobile Solid ^{4}He

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Disordered single crystals of solid ^{4}He contained inside a torsional oscillator behave as if part of the solid is decoupled from the oscillator. This effect persists up to temperatures as high as 1.9K. Overall, the behavior of these disordered crystals closely resembles the low temperature effects currently under debate regarding their interpretation in terms of supersolidity. Here, we report a systematic study of the temperature and stress dependence of the internal friction associated with this disordered solid. The study includes disordered crystals grown using commercially pure ^{4}He or a 100 ppm ^{3}He-^{4}He mixture. Based on results of our neutron scattering experiments, we model our disordered crystals as an array of grains separated by low angle grain boundaries. The decoupled mass in this picture results from the ability of slightly misoriented solid grains to slip past each other, and so lag the motion of the torsional oscillator. Our data fit the model very well. By fitting the data to specific forms, we were able to extract a characteristic energy scale associated with the internal friction. Our results support the idea that the friction mechanism associated with the motion inside the solid results from climb of individual dislocations.

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Solid ^{4}He shows some unusual properties at low temperatures. The atoms are highly non localized even at T=0, forming a quantum solid. As such, it has been suggested[1,2] that ^{4}He is a good candidate for a supersolid - a crystalline solid which can support mass superflow. Several experimental results during the past few years made that possibility seem more likely. Most of these experiments study solid ^{4}He contained inside a torsional oscillator (TO). The interpretation of those experiments, in which solid ^{4}He seems to move relative to the TO is currently a subject of controversy. One school of thought interprets the pioneering experiments of Kim and Chan (KC)[3] in terms of a supersolid scenario. On the other hand, measurements of the shear modulus[4] and recent TO experiments by Reppy[5] indicate that dislocations may play a more significant role than previously thought. Several theory papers[6,7] interpret these results using the Granato-Lucke model of a pinned dislocation tangle. These calculations are in broad agreement with experiments on polycrystalline samples, but so are models where the solid is taken to be glass-like[8]. Superclimb of dislocation[9] was also considered in conjunction with flow experiments through the solid[10]. What has been missing so far is a direct experimental evidence of a specific mechanism by which the solid can flow. The present work provides evidence in this direction, linking a specific kind of dislocation motion to a TO experiment. Like other groups[3,5,11–13], we use the TO technique. In contrast to other groups who study polycrystalline solid He, our approach is to study single crystals grown inside the TO. These crystals can be disordered in-situ resulting in an array of solid grains separated by low angle grain boundaries[14]. Once disordered, the resonant frequency of the TO changes as if some fraction of the mass of solid He became decoupled from the motion of the walls of the cell. In different crystals, we observed a decoupled mass fraction ranging between a few percent and up to 35%. It is important to stress that this effect takes place if and only if the cell is full of solid. With any liquid present in the cell, the single crystal is stable and the moment of inertia of the solid He is constant, in good agreement with what one would expect from a rigid body. Over the last few years, we grew single crystals over a wide temperature range (1.1K to 1.9K) and observed mass decoupling in all of them[15]. This temperature interval is wide enough to permit us to study the temperature dependence of the mobility and extract a relevant energy scale characterizing the dissipation associated with the mobile solid.

In the experiment, single crystals of 1cm^3 volume are grown at constant temperature and pressure inside an annular sample space of the TO. The inner radius of the annular sample space is 6.5 mm, the height is 10 mm, and its width is 2 mm (for additional details see[16]). We use an electrostatically driven TO. The applied torque τ_0 is related to the AC driving voltage V_0 through $\tau_0 = V_{DC} r_0 C V_0/d$, where $V_{DC} = 200V$ is a constant bias on one of the capacitor plates; $r_0 = 8.5mm$ is the radius of the outer wall of the cell; $C = 2pF$; and $d = 400\mu m$ is the distance between the capacitor plates. With a V_0 =1mV rms, the torque is $10^{-11} Nm$. Our expertise in growing single crystals comes from neutron scattering experiments done by our group[14]. In these experiments, we learned that the solid grows as a single crystal when the cell is slowly filled with He at a constant temperature and pressure on the melting curve. The time it takes to fill the cell with a single crystal ranges between several hours at temperatures below 1.5K to well over a day at temperatures around 2K. In order to enable the solid to fill the cell without leaving residual pockets of liquid[17,18] all internal corners of the sample space are intentionally rounded. The TO is thermally connected to a ^{3}He refrigerator through its torsion rod. Hence, the bottom of the cell inside the oscillator is the coldest internal surface and the solid nucleates there. The pressure inside the cell is measured in-situ using a capacitive pressure gauge attached to the top of the cell. This serves to ensure that we conduct measurements in the region of the phase diagram where the solid is the stable phase[15].

Once the cell is filled with solid He, we create structural disorder in the crystal, for example by cooling the cell by $\Delta T \sim 10mK$. Upon cooling, the crystal should contract. However, it is prevented from doing so by the rigid central post of the annulus, creating a strain of $\alpha\Delta$T and stress of G × strain. Here, α is the thermal expansion coefficient, and G is the shear modulus. Due to the large thermal expansion of the crystal (α ~10^{-2} K^{-1} at 1.6 K) and a small critical shear stress[4,19] (around 10^{-6} bar), cooling by 10mK is enough to exceed the critical stress and decompose the single crystal into an array of grains separated by low angle grain boundaries. The properties of such array were investigated in our neutron diffraction experiments using the Laue technique[14]. The typical angle between neighboring grains is a few degrees.

The onset of structural disorder influences the TO in a way shown in figure 1. First, the resonant frequency increases as if some of the solid He has decoupled from the oscillator. At the same time, the dissipation (Q^{-1}) increases sharply. Both effects can be explained if the solid He grains inside the cell are weakly coupled to each other. The interaction of He with any other solid (the wall) is much stronger than the He-He interaction. In addition, the walls are rough on an atomic scale. Consequently, the pinning of solid He grains at the walls of the cell is strong and they move with the TO. Away from the wall, the intergrain coupling is weaker and grains separated by low angle grain boundaries may be able to move relatively to each other. This ability of solid He crystallites to move and change their orientation inside a solid sample was first discovered in a neutron diffraction experiment by Pelleg et al.[14] and was later confirmed in an independent study[20]. The extent of the relative motion in our experiment is rather small. For example, let's consider a situation where one grain moves with the TO while the adjacent grain does not. With a typical tangential speed of the TO of 10 μm/sec, the maximal relative displacement would be less than 5 nm. Possible explanations as to how such motion can occur with ease include superfluidity of the grain boundaries[21], or glide of dislocations. As a result of the relative motion, the grains in the middle of the annulus can lag the motion of the walls, so that some of the He mass appears decoupled from the TO. At the same time the friction between grains which move relative to each other increases the dissipation Q^{-1}. Following the initial increase of Q^{-1} shown in panel (b) of figure 1, the dissipation decreases slowly with time, while the frequency continues to increase. This decrease of the dissipation can be interpreted as a result of the grains gradually reorienting themselves to lower the friction. We used such measurements of the structural relaxation following the disordering process (figure 1b)to learn about the size of the grains[16]. By comparing the characteristic relaxation time t_R of different crystals, we found that t_R of solid samples grown from 100 ppm ^{3}He-^{4}He mixture is longer than that of samples grown using pure ^{4}He. We attribute this difference to the fact that once the grains are formed, ^{3}He begins to diffuse from the bulk onto the grain boundaries. As long as the diffusion process continues, the relaxation is not complete. The characteristic dimension of a grain, $< x >$, can then be estimated using the relation $< x >= (Dt_R)^{1/2}$, where D is the diffusion coefficient. Using published values of D^{22} and our measured relaxation times, we estimate that the solid grains in the cell are a fraction of a mm in size . Their orientation remains close to that of the parent crystal[14].

Over the last few years, we grew and studied many tens of single crystals. The variation of the frequency and dissipation with temperature and external drive were similar for all of them. In this study, we collected and analyzed such data of 5 hcp crystals grown under a variety of conditions: (a) grown in the hcp phase from a normal fluid at some temperature above the upper triple point of 1.772K. (b) grown from the superfluid in the hcp phase below the lower triple point of 1.464K. (c) grown in the bcc phase at 1.65K, and then transformed into the hcp structure after having been cooled below the triple point at 1.46K. (d) same as (a) or (c), but grown from a ^{3}He-^{4}He mixture containing 100 ppm of ^{3}He instead of ^{4}He of commercial purity. The selection of a diverse variety of initial conditions for the crystal growth was intended to look for quantitatively similar features in their response to temperature and drive changes, independent of the growth procedure.

Since the disordered crystal is made up of grains a fraction of a mm in size, so as one moves across the 2 mm wide annulus, only a few grain boundaries are encountered. So, instead of the continuum non-local model of Nussinov et. al.[8], we chose to use a simpler, discrete model, in which the solid helium inside the annular sample space is divided into 2 parts (see figure 2). One part is in contact with the outer and inner walls, and contains grains which move with the walls. The second (inner) part contains grains which are weakly coupled with the outer part and can therefore move in relation to it. The solid in the middle part represents the decoupled mass. For the crystals used in this experiment, the decoupling process caused the moment of inertia of the solid to decrease by typically 30%. We remark in this context that we found that when adjacent grains are strongly misoriented (polycrystalline solid)[23], the amount of decoupled mass decreased to ~1%, similar to what is measured by other groups who study polycrystals[3,5,11–13].

We assume that all the grains in the inner part are dragged by friction with the outer part and move at an angular velocity $\dot{\theta_m}$ proportional to $\dot{\theta}$, the velocity of the cell. The relative slip in our model is represented by a phase lag α, namely $\dot{\theta_m} = \beta\dot{\theta}e^{-i\alpha}$ ($0 < \beta < 1$ is a con-

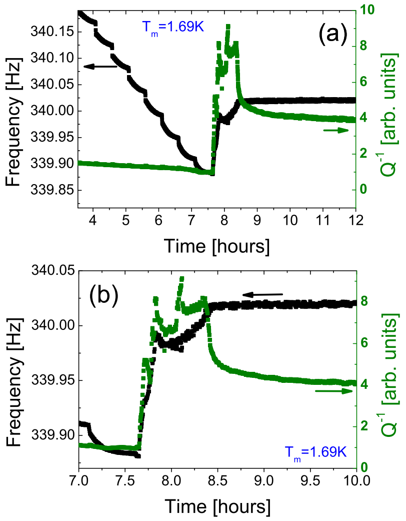

FIG. 1: (a) Typical time dependence of the resonant frequency and dissipation of a cell containing a bcc crystal during the final stages of crystal growth. Initially, the frequency decreases and the Q increases as He is added to the cell in small steps. At 7.7 hours from the beginning of the growth, the cell is full of solid and the crystal spontaneously disorders. The resonant frequency increases as if 30% of the He mass has decoupled from the TO. The dissipation (Q^{-1}) first increases sharply, and then decreases with time to about half the maximal value as the crystal reaches a steady state. Panel (b) shows the response of the TO during and after the disordering stage on an expanded scale.

stant). The friction force between the mobile and immobile grains is assumed to depend linearly on the relative velocity $\dot{\theta} - \dot{\theta}_m$, with an effective friction coefficient between the different parts of γ_2. Denoting the moment of inertia of the cell with the grains rigidly attached to it by I, we can write the equation of motion of the cell.

$$I\ddot{\theta} + \gamma_1\dot{\theta} + \gamma_2(\dot{\theta} - \beta\dot{\theta}e^{-i\alpha}) + \kappa\theta = \tau_0 e^{i\omega t} \qquad (1)$$

Here τ_0 is the external driving torque, κ is the torsion constant of the rod, and $\gamma_1\dot{\theta}$ is the friction of the TO cell and the grains attached to it.

We consider the case where the friction associated with the intergrain motion is much lower than the internal friction within the solid moving with the cell, namely $\gamma_1 \gg \gamma_2(1-\beta cos(\alpha))$. We also take $\omega_0 \gg \gamma_2\beta sin(\alpha)/2I$. Both these assumption hold for our system. In this case, the solution of equation 1 yields the resonant frequency ω_α and amplitude θ_0.

$$\omega_\alpha \approx \omega_0 - \beta\gamma_2 sin(\alpha)/2I. \qquad (2)$$

$$\theta_0 \approx \tau_0/\omega_0\gamma_1 - \tau_0/\omega_0\gamma_1(\gamma_2/\gamma_1)(1-\beta cos(\alpha)) \qquad (3)$$

Here $\omega_0 = \sqrt{\kappa/I}$. In our model, the phase lag α should increase with the relative velocity which in turn increases

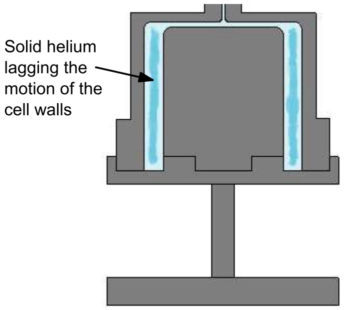

FIG. 2: A schematic cross section of the TO with the annular sample space filled with disordered solid. The outer and inner walls of the annulus oscillate together. In our model, we divide the solid into 2 parts; one part includes grains strongly attached to the outer and inner walls. This part of the solid moves with the walls. The second part, marked by the arrow, is weakly coupled to the walls and to the solid moving with the walls. This part lags the motion of the walls.

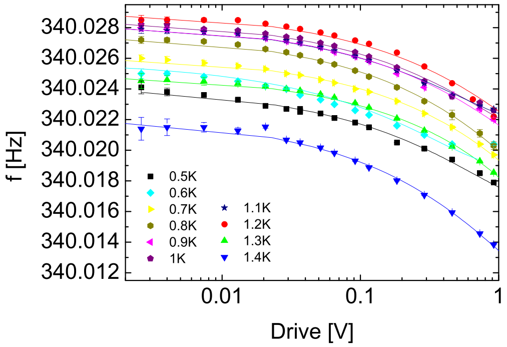

FIG. 3: Resonant frequency of the TO containing an hcp crystal grown of 100ppm ^{3}He-^{4}He mixture, as function of the driving AC voltage. This particular crystal was initially grown in the bcc phase at 1.65K and transformed into the hcp structure at 1.46K. Data sets are for different temperatures. Solid lines are fits to equation 2 with $\alpha \propto \sqrt{\tau_0}$.

with the applied torque. To find this dependence, in figure 3 we plot the resonant frequency of the cell as function of the applied AC voltage. The small offsets between different curves are due to temperature dependence of ω_0 which are taken as given. The data were fit to equation 2. We found that data sets at different temperatures all have the same dependence on the external torque. The solid lines shown in figure 3 were obtained by taking the phase lag α to depend linearly on $\sqrt{\tau_0}$, with no temperature dependence. Obviously, the fit is good. We remark in this context that in a classical model of a dislocation gliding with a speed v through a periodic (Peierls) potential (see Nabarro[24], ch. VII), the dislocation radiates energy in the form of sound. This mechanism causes the speed v to increase as the square root of the applied

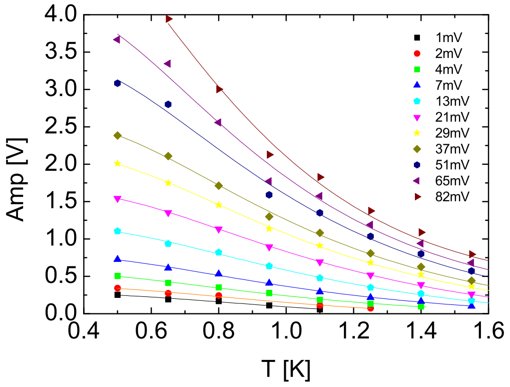

FIG. 4: Amplitude of oscillations at a constant drive as function of temperature, for a ^{4}He hcp crystal grown at 1.83K. The various data sets are labelled by different values of the AC drive. The solid lines are fits to Eq. 3, with the friction coefficient γ_2 taken from Eq. 4.

stress.

We next fit the data of the resonant amplitude θ_0. The first term in equation 3, $\tau_0/\omega_0\gamma_1$, is the amplitude for the case where the solid moves with the cell. From fitting the data we find that this term is linear in the external torque and has the same magnitude as the measured resonant amplitude of the TO with the cell full of an annealed crystal. Hence, the first term indeed represents the resonant amplitude of the cell and of the solid helium attached to the walls. The second term in equation 3 decreases the resonant amplitude due to intergrain friction. In our model, the temperature dependence of this term is contained in the intergrain friction coefficient γ_2. We found that the temperature dependence of the oscillation amplitude at a fixed external torque can be fit using γ_2 given by

$$\gamma_2 = \eta \frac{e^{-W_0/k_B T}}{k_B T} \tag{4}$$

Here, η and W_0 are fitting parameters. This particular form describes the velocity of dislocations during climb via vacancy emission/absorption by jogs[25]. The energy W_0 is the characteristic energy scale associated with this process. In figure 4 we show the fit of the temperature dependence of θ_0 for a typical set of data, here for an hcp crystal grown at 1.83K and cooled by 0.15K steps down to 0.5K. The different sets of data are for different values of the external torque. Equation 3 with γ_2 given by equation 4 fits our data very well over the whole temperature range (0.5K-1.8K), over 2 orders of magnitude in the driving torque, and for all the crystals which analyzed in this work. Figure 5 shows the values of W_0 for all the crystals. We found that these values fall into two groups. For hcp crystals grown using commercially pure ^{4}He we find W_0 ∼3.0K at small stress. For crystals grown initially as bcc or from a ^{3}He-^{4}He mixture, W_0 ∼5.8K. The fact that W_0 takes only two distinct values indicates that crystals grown by the same procedure grow with a very similar orientation. At the same token, crystals grown by different procedures have somewhat different orientations and a different value of W_0. For completeness, we have also tried other functional forms for γ_2, including among others an Arrhenius type exponential dependence and a power law in temperature. The extended temperature range over which we can fit the data enabled us to clearly discriminate between the various forms, and state that none of these fit the data nearly as well.

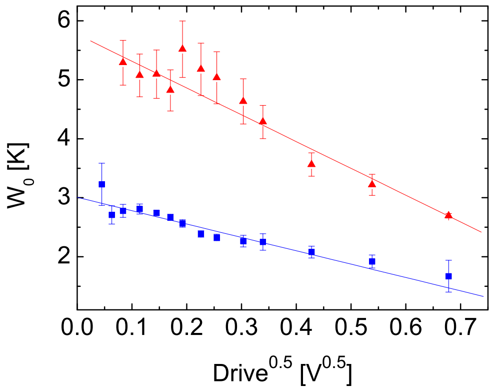

FIG. 5: Characteristic energy W_0 vs. the square root of the driving voltage for different crystals. W_0 was obtained from fitting the data to Eq. 4. Blue squares are the combined data of two hcp crystals, one grown at 1.83K and the second at 1.37K. The red triangles are the combined data of three crystals, one grown as bcc at 1.69K and then cooled into the hcp phase through the lower triple point, and two crystals grown from a 100ppm ^{3}He-^{4}He mixture, one at 1.65K and the other at 1.8K. Solid lines are a linear fit.

Figure 5 also shows that W_0 decreases with stress in proportion to the square root of the stress (external torque). In the theory of dislocations[25], such a decrease results from the dependence of the vacancy formation process on stress. We remark that climb of dislocations requires an emission/absorption of vacancies at the core of the dislocation. The local stress in or near the core is significant, affecting the formation energy of the vacancy. This formation energy was calculated by Pollet et al.[26]. In their simulations, it was found that in solid He under stress the formation energy is much lower than in a perfect solid, and similar to the values of W_0 which we found. Recently, Suhel and Beamish[27] found an activation energy of 5.1K characterizing the structural relaxation of an hcp polycrystal. Incidentally, the calculated energy of a jog in solid He is 5.8K[28]. All these values, together with the values of W_0 which we found, set the characteristic energy scale associated with structural changes in the solid.

Regarding the differences between crystals grown from a ^{3}He-^{4}He mixture and those grown using pure ^{4}He: except for affecting the value of W_0 as shown in Figure 5, the presence of 100ppm of ^{3}He in the solid also reduces the amplitude of oscillations at low temperatures and small values of the driving torque. At high drive, the amplitude is unaffected by the presence of ^{3}He. The binding energy of ^{3}He atoms to dislocations was estimated as 0.43K[29] and 0.7K in another paper[30]. It is therefore probable that the mobility of dislocations below 1K is reduced in the presence of ^{3}He atoms, as these increasingly become bound to the dislocations upon cooling the crystal. At high enough stress, dislocations break away from these pinning sites and the ^{3}He has no effect, in agreement with previous experiments[30,31].

To conclude, it seems that the dissipation in disordered ^{4}He crystals above 0.5K can be successfully modelled by assuming a small effective friction at interfaces. In disordered single crystals used in our experiments, these interfaces are low angle grain boundaries. They can therefore be described by a set of dislocations. The fact that a well defined energy scale W_0 emerges from fitting the data indicates that the orientation of all internal interfaces is indeed very similar, meaning that the disordered crystal remains closely related to the parent single crystal. Further, the absence of pinning at these relatively high temperature allows us to observe response associated with individual dislocations rather than those of a pinned dislocation tangle. The low value of the grain-grain dissipation responsible for the mass decoupling effect is still a puzzle. It can arise either from a superfluid behaviour of the grain boundaries , or from dislocation glide. The dependence of the phase lag angle on the external drive, $\alpha \propto \sqrt{\tau_0}$ which we found may offer some clue with respect to this question. Regarding the possibility that the grain boundaries are superfluid as predicted by Pollet et al.,[21], we do not see any change in the response of our disordered crystals, such as a sign of a critical temperature, even for solids grown at 1.9K. This observation implies that interfacial superfluidity, if it exists, should persist at temperatures higher than 1.9K.

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